

## High precision integrated circuit capacitors

### ABSTRACT OF THE INVENTION

5        A polysilicon layer (30) is formed on a dielectric region  
(20). An optional metal silicide layer (50) can be formed on the  
polysilicon layer. A dielectric layer (60) is formed over the  
metal silicide layer and a conductive layer (70) formed over the  
dielectric layer. The formed layers are etched by a combination  
10 of multi-step dry and wet process to form high precision  
integrated circuit capacitors.